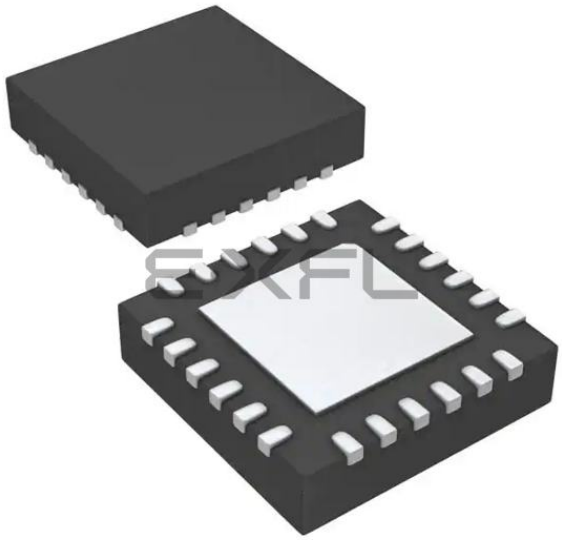

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, UART/USART
Peripherals	LVD, POR, WDT
Number of I/O	15
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 6x8/12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	24-WFQFN Exposed Pad
Supplier Device Package	24-HWQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1177agna-w0

1.6 Outline of Functions

Remark This outline describes the functions at the time when Peripheral I/O redirection register 0 (PIOR0) are set to 00H.

(1/2)

<R>

Item		20-pin	24-pin	30-pin	32-pin	48-pin
		R5F1176x (x = 8, A)	R5F1177x (x = 8, A)	R5F117Ax (x = 8, A, C)	R5F117Bx (x = A, C)	R5F117Gx (x = A, C)
Code flash memory (KB)		8 to 16 KB	8 to 16 KB	8 to 32 KB	16 to 32 KB	16 to 32 KB
Data flash memory (KB)		2 KB	2 KB	2 KB	2 KB	2 KB
RAM		0.7 to 2.0 KB	0.7 to 2.0 KB	0.7 to 3.0 KB Note	2.0 to 3.0 KB Note	2.0 to 3.0 KB Note
Address space		1 MB				
Main system clock	High-speed system clock (f_{MX})	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode:1 to 20 MHz (V_{DD} = 2.7 to 3.6 V), HS (High-speed main) mode:1 to 16 MHz (V_{DD} = 2.4 to 3.6 V), LS (Low-speed main) mode:1 to 8 MHz (V_{DD} = 1.8 to 3.6 V), LV (Low-voltage main) mode:1 to 4 MHz (V_{DD} = 1.6 to 3.6 V), LP (Low-power main) mode:1 MHz (V_{DD} = 1.8 to 3.6 V)				
	High-speed on-chip oscillator clock (f_{IH}) Max: 24 MHz	HS (High-speed main) mode: 1 to 24 MHz (V_{DD} = 2.7 to 3.6 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 3.6 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 3.6 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 3.6 V), LP (Low-power main) mode: 1 MHz (V_{DD} = 1.8 to 3.6 V)				
	Middle-speed on-chip oscillator clock (f_{IM}) Max: 4 MHz					
Subsystem clock	Subsystem clock oscillator (f_{SX}, f_{SXR})	—		XT1 (crystal) oscillation 32.768 kHz (TYP.): V_{DD} = 1.6 to 3.6 V		
	Low-speed on-chip oscillator clock (f_{IL})	15 kHz (TYP.): V_{DD} = 1.6 to 3.6 V				
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)				
Minimum instruction execution time		0.04167 μs (High-speed on-chip oscillator clock: f_{IH} = 24 MHz operation)				
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)				
		—		30.5 μs (Subsystem clock oscillator clock: f_{SX} = 32.768 kHz operation)		
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.				
I/O port	Total	14	18	24	26	42
	CMOS I/O	11	15	19	21	33
	CMOS input	3	3	5	5	5
	N-ch open-drain I/O (6 V tolerance)	—	—	—	—	4
Timer	16-bit timer	4 channels				
	Watchdog timer	1 channel				
	Real-time clock	1 channel				
	12-bit interval timer	1 channel				
	8/16-bit interval timer	4 channels (8 bit) / 2 channels (16 bit)				
	Timer output	2	4	3	4	4
	RTC output	—		1 channel • 1 Hz (subsystem clock generator and RTC/other clock: f_{SX} = 32.768 kHz)		

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.

R5F117xC (x = A, B, G): Start address FF300H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

(2/2)

Item		20-pin R5F1176x (x = 8, A)	24-pin R5F1177x (x = 8, A)	30-pin R5F117Ax (x = 8, A, C)	32-pin R5F117Bx (x = A, C)	48-pin R5F117Gx (x = A, C)
Clock output/buzzer output		1	1	1	1	2
		[20-pin, 24-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) [30-pin, 32-pin, 48-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (subsystem clock generator and RTC/other clock: f_{SXR} = 32.768 kHz operation)				
12-bit resolution A/D converter		6 channels	6 channels	12 channels	12 channels	17 channels
Comparator (Window Comparator)		2 channels				
Operational amplifier		2 channels		4 channels		
Data Operation Circuit (DOC)		Comparison, addition, and subtraction of 16-bit data				
Serial interface		[20-pin, 30-pin products] • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel [24-pin, 32-pin, 48-pin products] • CSI: 2 channels/UART: 1 channel/simplified I^2C: 2 channels				
<R> Data transfer controller (DTC)		16 sources	20 sources	19 sources	20 sources	22 sources
<R> Event link controller (ELC)		Event input: 15 Event trigger output: 5	Event input: 17 Event trigger output: 5	Event input: 17 Event trigger output: 7	Event input: 17 Event trigger output: 7	Event input: 20 Event trigger output: 7
Vectored interrupt sources	Internal	22	22	24	24	24
	External	3	5	5	5	8
Key interrupt		—	3	—	3	4
Reset		• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution Note • Internal reset by RAM parity error • Internal reset by illegal-memory access				
Power-on-reset circuit		• Power-on-reset: 1.51 ± 0.04V (T_A = -40 to +85°C) • Power-down-reset: 1.50 ± 0.04 V (T_A = -40 to +85°C)				
Voltage detector	Power on	1.67 V to 3.13 V (12 stages)				
	Power down	1.63 V to 3.06 V (12 stages)				
On-chip debug function		Provided (Enable to tracing)				
Power supply voltage		V_{DD} = 1.6 to 3.6 V				
Operating ambient temperature		T_A = -40 to +105°C				

The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS

Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/I1D User's Manual.

Caution 3. Please contact Renesas Electronics sales office for derating of operation under T_A = +85 to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Caution 4. When operating temperature exceeds 85°C, only HS (high-speed main) mode can be used as the flash operation mode. Regulator mode should be used with the normal setting (MCSEL = 0).

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)
(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/5)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	I_{OH1}	Per pin for P00 to P04, P30 to P33, P40, P50 to P57, P130	T_A = -40 to +85°C			-10.0 Note 2	mA
			T_A = +85 to +105°C			-3.0 Note 2	mA
		Total of P00 to P04, P40, P130 (When duty ≤ 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			-10.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			-5.0	mA
			1.6 V ≤ V_{DD} < 1.8 V			-2.5	mA
		Total of P30 to P33, P50 to P57 (When duty ≤ 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			-19.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			-10.0	mA
			1.6 V ≤ V_{DD} < 1.8 V			-5.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				-29.0	mA
	I_{OH2}	Per pin for P10 to P17, P20 to P25				-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ V_{DD} ≤ 3.6 V			-1.4	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = -10.0 mA
Total output current of pins = (-10.0 × 0.7)/(80 × 0.01) ≈ -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.
A current higher than the absolute maximum rating must not flow into one pin.

Caution P30 and P51 to P56 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(2/4)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	Subsystem clock operation	f_{SX} = 32.768 kHz, T_A = -40°C Note 4	Normal operation	Square wave input		3.2	6.1	μA
						Resonator connection		3.3	6.1	
				f_{SX} = 32.768 kHz, T_A = +25°C Note 4	Normal operation	Square wave input		3.4	6.1	
						Resonator connection		3.6	6.1	
				f_{SX} = 32.768 kHz, T_A = +50°C Note 4	Normal operation	Square wave input		3.5	6.7	
						Resonator connection		3.7	6.7	
				f_{SX} = 32.768 kHz, T_A = +70°C Note 4	Normal operation	Square wave input		3.7	7.5	
						Resonator connection		3.9	7.5	
				f_{SX} = 32.768 kHz, T_A = +85°C Note 4	Normal operation	Square wave input		4.0	8.9	
						Resonator connection		4.2	8.9	
				f_{SX} = 32.768 kHz, T_A = +105°C Note 4	Normal operation	Square wave input		4.5	21.0	
						Resonator connection		4.7	21.1	
				f_{IL} = 15 kHz, T_A = -40°C Note 6	Normal operation			1.8	5.9	
				f_{IL} = 15 kHz, T_A = +25°C Note 6	Normal operation			1.9	5.9	
				f_{IL} = 15 kHz, T_A = +85°C Note 6	Normal operation			2.3	8.7	
				f_{IL} = 15 kHz, T_A = +105°C Note 6	Normal operation			3.0	20.9	

<R> **Note 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The MAX values include the peripheral operating current. However, these values do not include the current flowing into the A/D converter, operational amplifier, comparator, LVD circuit, I/O ports, and on-chip pull-up/pull-down resistors, and the current flowing during data flash rewrite.

Note 2. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Note 3. When the high-speed system clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Note 4. When the high-speed system clock, high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped. When ultra-low-power consumption oscillation is set (AMPHS1, AMPHS0) = (1, 0). The values do not include the current flowing into the real-time clock, 12-bit interval timer, and watchdog timer.

Note 5. When the high-speed system clock, high-speed on-chip oscillator clock, sub clock, and low-speed on-chip oscillator clock are stopped. The MAX values include the current of peripheral operation except BGO operation, and the STOP leakage current. However, the real time clock, watchdog timer, LVD circuit, and A/D converter are stopped.

Note 6. When the high-speed system clock, high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, and sub clock are stopped.

Note 7. When the high-speed system clock, high-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{IH}: High-speed on-chip oscillator clock frequency (24 MHz max.)

Remark 3. f_{IM}: Middle-speed on-chip oscillator clock frequency (4 MHz max.)

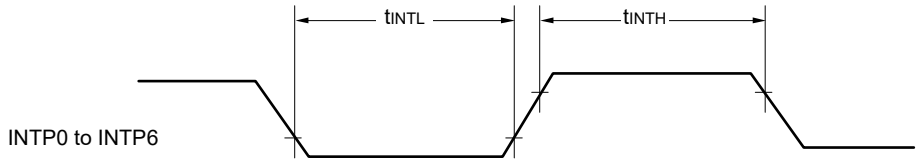
Remark 4. f_{IL}: Low-speed on-chip oscillator clock frequency

Remark 5. f_{SX}: Sub clock frequency (XT1 clock oscillation frequency)

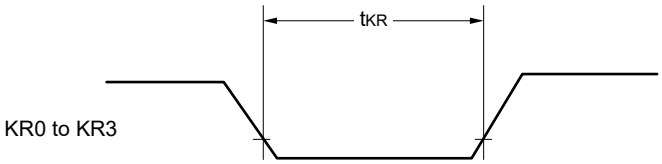
Remark 6. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency or low-speed on-chip oscillator clock frequency)

Remark 7. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

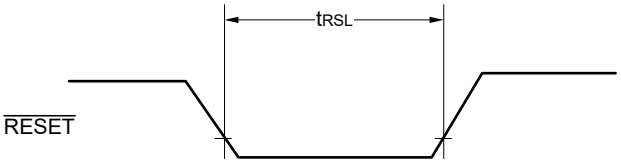
Interrupt Request Input Timing



Key Interrupt Input Timing



$\overline{\text{RESET}}$ Input Timing



(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

(T_A = +85 to +105°C, 2.7 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/4$	2.7 V ≤ V_{DD} ≤ 3.6 V	250		ns
			2.4 V ≤ V_{DD} ≤ 3.6 V	500		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY1}/2 - 36		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		t_{KCY1}/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V		66		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		133		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}			38		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note 4			50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00, 01))

(6) Communication at different potential (1.8 V, 2.5V) (UART mode) (dedicated baud rate generator output)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate Note 2		Transmission	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 2	Mbps
			2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		Notes 3, 4	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 5	Mbps

Note 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} ≤ 3.6 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. Use it with $V_{DD} \geq V_b$.

Note 4. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.4 V ≤ V_{DD} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

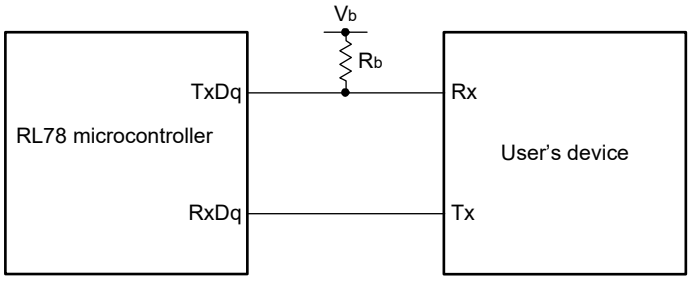
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

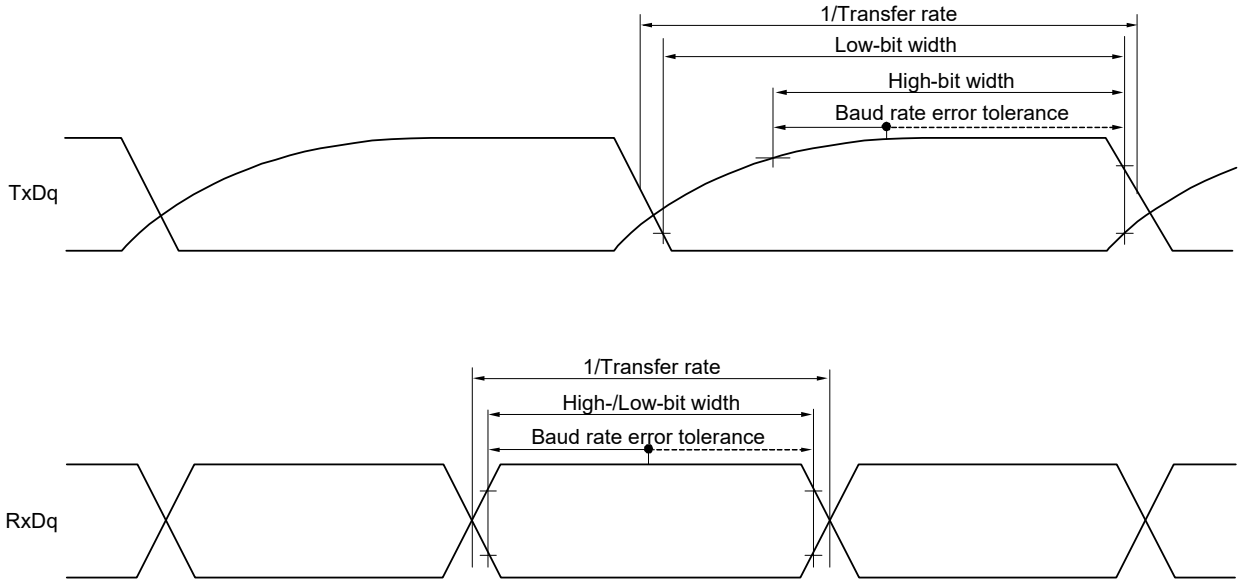
Note 5. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 4 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Remark 1. R_b[Ω]: Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

Remark 2. q: UART number (q = 0), g: PIM and POM number (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(7) Communication at different potential (2.5 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85°C, 2.7 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/2$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300		1500		1500		1500		ns
SCKp high-level width	t_{KH1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		ns
SCKp low-level width	t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 10		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121		479		479		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			130		130		130		130	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		33		110		110		110		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10		10		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			10		10		10		10	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

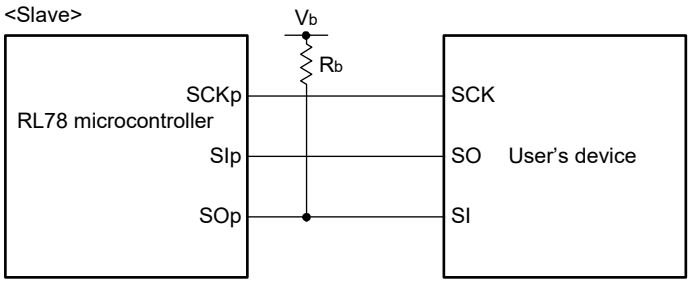
(9) Communication at different potential (1.8 V, 2.5 V) (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to 85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	t_{KCY2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V	20 MHz < f_{MCK} ≤ 24 MHz	16/f_{MCK}		—		—		—		ns
			16 MHz < f_{MCK} ≤ 20 MHz	14/f_{MCK}		—		—		—		ns
			8 MHz < f_{MCK} ≤ 16 MHz	12/f_{MCK}		—		—		—		ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}		—		—		ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	20 MHz < f_{MCK} ≤ 24 MHz	36/f_{MCK}		—		—		—		ns
			16 MHz < f_{MCK} ≤ 20 MHz	32/f_{MCK}		—		—		—		ns
			8 MHz < f_{MCK} ≤ 16 MHz	26/f_{MCK}		—		—		—		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		16/f_{MCK}		—		—		ns
			f_{MCK} ≤ 4 MHz	10/f_{MCK}		10/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		t_{KCY2}/2 - 18		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		ns
SIp setup time (to SCKp↑) Note 3	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
SIp hold time (from SCKp↑) Note 4	t_{KSI2}			1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
Delay time from SCKp↓ to SOp output Note 5	t_{KSO2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ			2/f_{MCK} + 214		2/f_{MCK} + 573		2/f_{MCK} + 573		2/f_{MCK} + 573	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ			2/f_{MCK} + 573		2/f_{MCK} + 573		2/f_{MCK} + 573		2/f_{MCK} + 573	ns

(**Notes** and **Caution** are listed on the next page. **Remarks** are listed on the page after the next page.)

CSI mode connection diagram (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Note 2. Use it with $V_{DD} \geq V_b$.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

(3) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), conversion target: ANI16 to ANI18, internal reference voltage, temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V ≤ VDD ≤ 3.6 V, 1.6 V ≤ AVREFP ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		12	bit
			1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±7.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±3.0	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	4.125			µs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	9.5			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	57.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	3.3125			
			1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	7.875			
			1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V	54.25			
Zero-scale error Note 3	EZS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.5	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.5	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±3.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	LSB
		10-bit resolution	1.8 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AVREFP ≤ AVDD ≤ 3.6 V			±1.5	
Analog input voltage	VAIN			0		AVREFP	V
		Internal reference voltage (1.8 V ≤ VDD ≤ 3.6 V)		VBGR Note 4			
		Temperature sensor output voltage (1.8 V ≤ VDD ≤ 3.6 V)		VTMP25 Note 4			

Note 1. Cannot be used for lower 2 bits of ADCR register

Note 2. Cannot be used for lower 4 bits of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Note 4. Refer to **2.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution Always use AVDD pin with the same potential as the VDD pin.

(5) When reference voltage (+) = Internal reference voltage (1.45 V) (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI13, ANI16 to ANI18

(T_A = -40 to +85°C, 1.8 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = internal reference voltage, Reference voltage (-) = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tCONV	8-bit resolution	16			µs
Zero-scale error Note	EZS	8-bit resolution			±4.0	LSB
Integral linearity error Note	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note	DLE	8-bit resolution			±2.5	LSB
Analog input voltage	VAIN		0		V_{BGR}	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(6) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), conversion target: ANI2 to ANI13

(T_A = +85 to +105°C, 2.4 V ≤ AV_{REFP} ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8		12	bit
Overall error Note	AINL	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	3.375			µs
Zero-scale error Note	EZS	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	LSB
Full-scale error Note	EFS	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	LSB
Integral linearity error Note	ILE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	LSB
Differential linearity error Note	DLE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.5	LSB
Analog input voltage	VAIN			0		AV_{REFP}	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(2) LVD Detection Voltage of Interrupt & Reset Mode

(T_A = -40 to +85°C, $V_{PDR} \le AV_{DD} = V_{DD} \le 3.6$ V, $V_{SS} = AV_{SS} = 0$ V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVDA0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 0, 0, falling reset voltage		1.60	1.63	1.66	V
	V_{LVDA1}	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
			Falling interrupt voltage	1.70	1.73	1.77	V
	V_{LVDA2}	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
			Falling interrupt voltage	1.80	1.84	1.87	V
	V_{LVDA3}	LVIS0, LVIS1 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVDB0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 0, 1, falling reset voltage		1.80	1.84	1.87	V
	V_{LVDB1}	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
			Falling interrupt voltage	1.90	1.94	1.98	V
	V_{LVDB2}	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
			Falling interrupt voltage	2.00	2.04	2.08	V
	V_{LVDB3}	LVIS0, LVIS1 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
			Falling interrupt voltage	3.00	3.06	3.12	V
	V_{LVDC0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 1, 0, falling reset voltage		2.40	2.45	2.50	V
	V_{LVDC1}	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
			Falling interrupt voltage	2.50	2.55	2.60	V
	V_{LVDC2}	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
			Falling interrupt voltage	2.60	2.65	2.70	V
	V_{LVDD0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 1, 1, falling reset voltage		2.70	2.75	2.81	V
	V_{LVDD1}	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVDD2}	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
			Falling interrupt voltage	2.90	2.96	3.02	V

(T_A = +85 to +105°C, $V_{PDR} \le AV_{DD} = V_{DD} \le 3.6$ V, $V_{SS} = AV_{SS} = 0$ V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVDD0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 1, 1, falling reset voltage		2.64	2.75	2.86	V
	V_{LVDD1}	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
			Falling interrupt voltage	2.75	2.86	2.97	V
	V_{LVDD2}	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V

2.6.7 Power supply voltage rising slope characteristics

(T_A = -40 to +105°C, $V_{SS} = AV_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

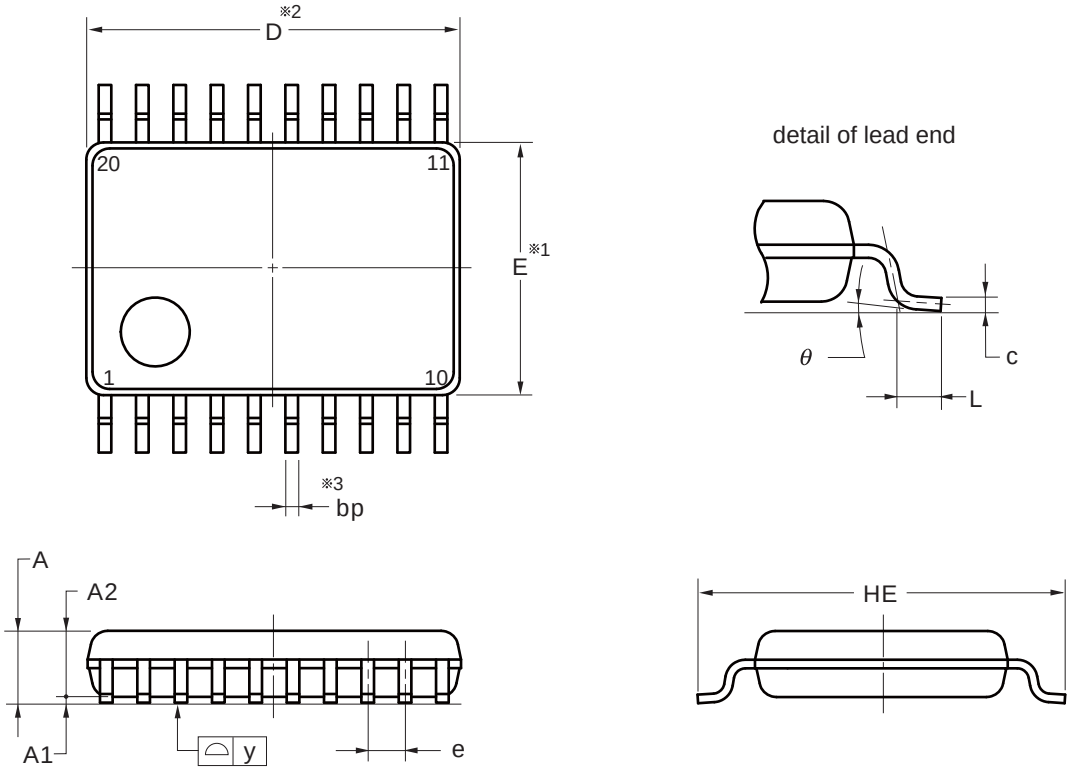
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

3. PACKAGE DRAWINGS

3.1 20-pin products

R5F1176AGSP, R5F11768GSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1



(UNIT:mm)

ITEM	DIMENSIONS
D	6.50±0.10
E	4.40±0.10
HE	6.40±0.20
A	1.45 MAX.
A1	0.10±0.10
A2	1.15
e	0.65±0.12
bp	$0.22^{+0.10}_{-0.05}$
c	$0.15^{+0.05}_{-0.02}$
L	0.50±0.20
y	0.10
θ	0° to 10°

NOTE

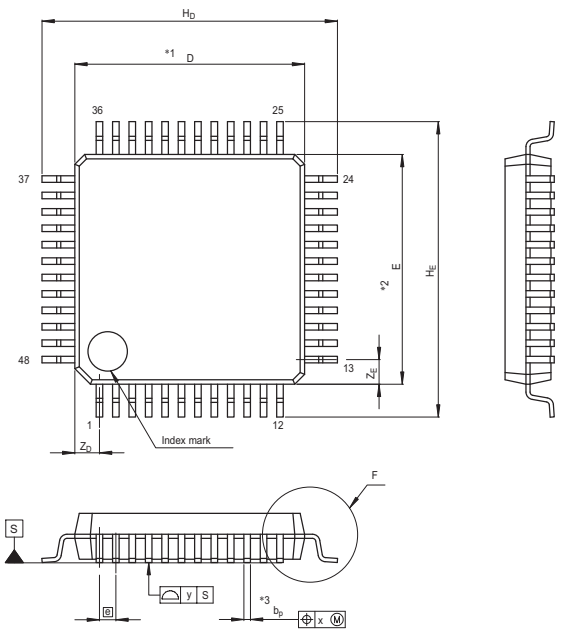
1.Dimensions "※1" and "※2" do not include mold flash.

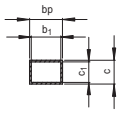
2.Dimension "※3" does not include trim offset.

3.5 48-pin products

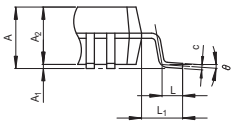
<R> R5F117GCGFB, R5F117GAGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LFQFP48-7x7-0.50	PLQP0048KB-A	48P6Q-A	0.2g





Terminal cross section



Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.9	7.0	7.1
E	6.9	7.0	7.1
A_2	—	1.4	—
H_D	8.8	9.0	9.2
H_E	8.8	9.0	9.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.17	0.22	0.27
b_1	—	0.20	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.10
Z_D	—	0.75	—
Z_E	—	0.75	—
L	0.35	0.5	0.65
L_1	—	1.0	—

REVISION HISTORY	RL78/I1D Datasheet

Rev.	Date	Description	
		Page	Summary
1.00	Aug 29, 2014	—	First Edition issued
2.00	Jan 16, 2015	24, 25, 27	Addition of note 7 in 2.3.2 Supply current characteristics
		24, 26	Addition of description in 2.3.2 Supply current characteristics
		26, 28	Modification of description in 2.3.2 Supply current characteristics
		28	Correction of error in 2.3.2 Supply current characteristics
		95	Modification of package drawing in 3.2 24-pin products
2.20	Feb 20, 2017	ALL	The function name changed from real-time clock to real-time clock 2
		5	Addition of product name in 1.3.1 20-pin products
		6	Addition of product name in 1.3.2 24-pin products
		7	Addition of product name in 1.3.3 30-pin products
		8	Addition of product name in 1.3.4 32-pin products
		9	Change of description and addition of product name in 1.3.4 32-pin products
		10	Addition of product name in 1.3.5 48-pin products
		13, 14	Change of description in 1.6 Outline of Functions
		16	Change of 2.1 Absolute Maximum Ratings
		22	Change of 2.3.1 Pin characteristics
		24	Change of conditions in 2.3.2 Supply current characteristics
		25, 27, 28	Change of note 1 in 2.3.2 Supply current characteristics
		26	Change of conditions and unit in 2.3.2 Supply current characteristics
		30	Change of note 3 in 2.3.2 Supply current characteristics
		31	Addition of note 5 in 2.3.2 Supply current characteristics
		92	Change of table in 2.8 Flash Memory Programming Characteristics
		92	Addition of note 4 in 2.8 Flash Memory Programming Characteristics
		99	Change of package drawing in 3.5 48-pin products

NOTES FOR CMOS DEVICES

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).

(2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

(3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.